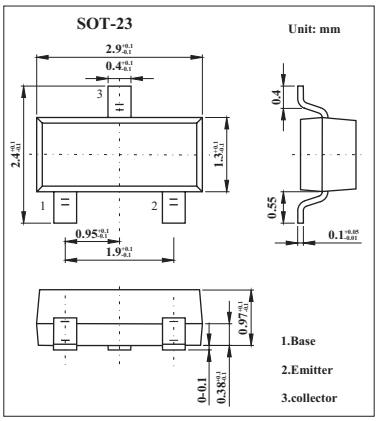
Medium Power Transistor

FMMT551



■ Features

- 60 Volt V_{CEO}.
- 1 Amp continuous current.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-80	V
Collector-emitter voltage	V_{CEO}	-60	V
Emitter-base voltage	V_{EBO}	-5	V
Peak collector current	I_{CM}	-2	A
Collector current	I_C	-1	A
Base current	I_B	-200	mA
Power dissipation	P_{tot}	500	mW
Operating and storage temperature range	T_j,T_{stg}	-55 to +200	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100μA	-80			V
Collector-emitter breakdown voltage *	$V_{(BR)CEO}$	I_C=-10mA	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100μA	-5			V
Collector cutoff current	I_{CBO}	V_{CB}=-60V			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-4V			0.1	μA
Collector-emitter saturation voltage *	$V_{CE(sat)}$	I_C=-150mA,I_B=-15mA			-0.35	V
Base-emitter saturation voltage *	$V_{BE(sat)}$	I_C=-150mA,I_B=-15mA			-1.1	V
Static Forward CurrentTransfer Ratio *	h_{FE}	I_C=-150mA,V_{CE}=-10V	50		150	
		I_C=-1A, V_{CE}=-10V	10			
Current-gain-bandwidth product	f_T	I_C=-50mA,V_{CE}=-10V,f=100MHz	150			MHz
Output capacitance	C_{obo}	V_{CB}=-10V,f=1MHz			25	pF

* Pulse test: tp ⩽ 300 μs; d ⩽ 0.02.

■ Marking

Marking	551